



ASML

EUV Lithography Towards Industrialization

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Dublin Meeting November 2014

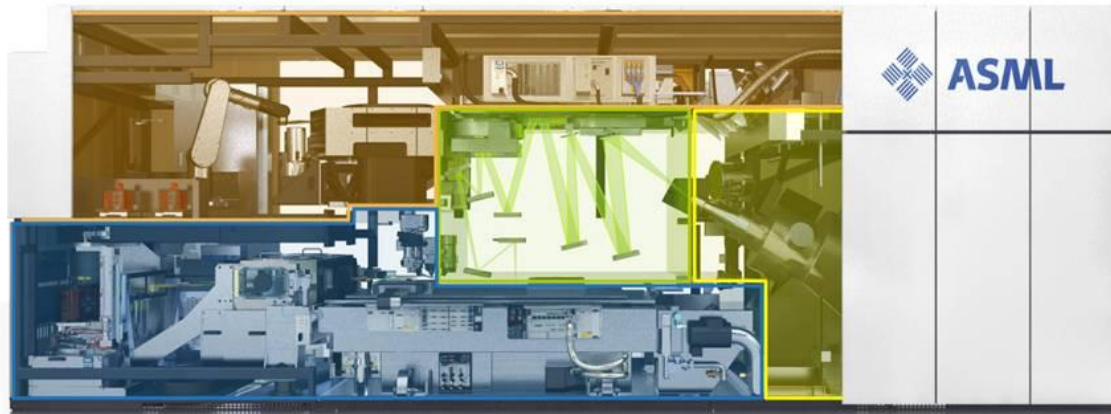
Agenda

- EUV benefit and status at customers
- Towards higher productivity
- Summary



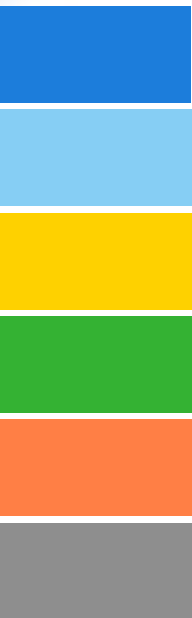
Agenda

- **EUV benefit and status at customers**



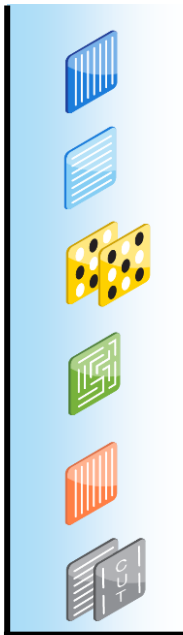
Multi-patterning complexity drives need for EUV

EUV Lithography will stop the strong increase of litho steps/masks needed



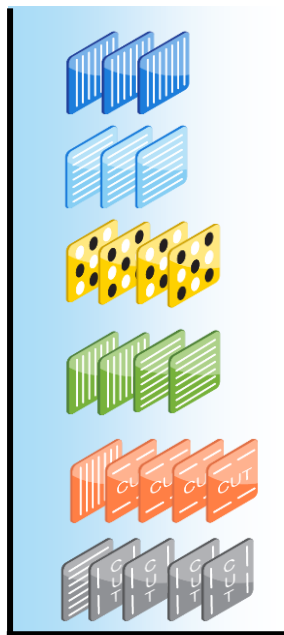
Layers

20 nm (Immersion)



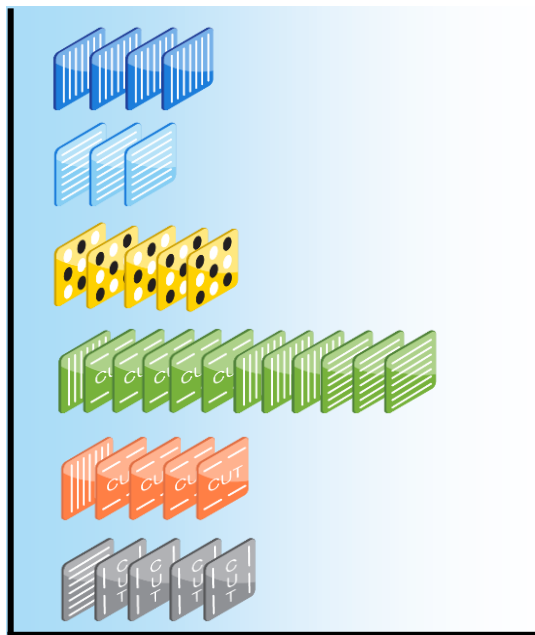
8xMasks

10 nm (Immersion)



23xMasks

7 nm (Immersion)



33xMasks

7nm (EUV)



9xMasks

Node

of litho steps

OVL Metrology

max metrology / litho steps

20 nm

8 (Immersion)

9-11

2

10 nm

23 (Immersion)

36-40

3

7 nm

33 (Immersion)

59-65

4

7 nm

9 (EUV)

12

3

EUV status:

Demonstrated >500 wafers per day at customer sites



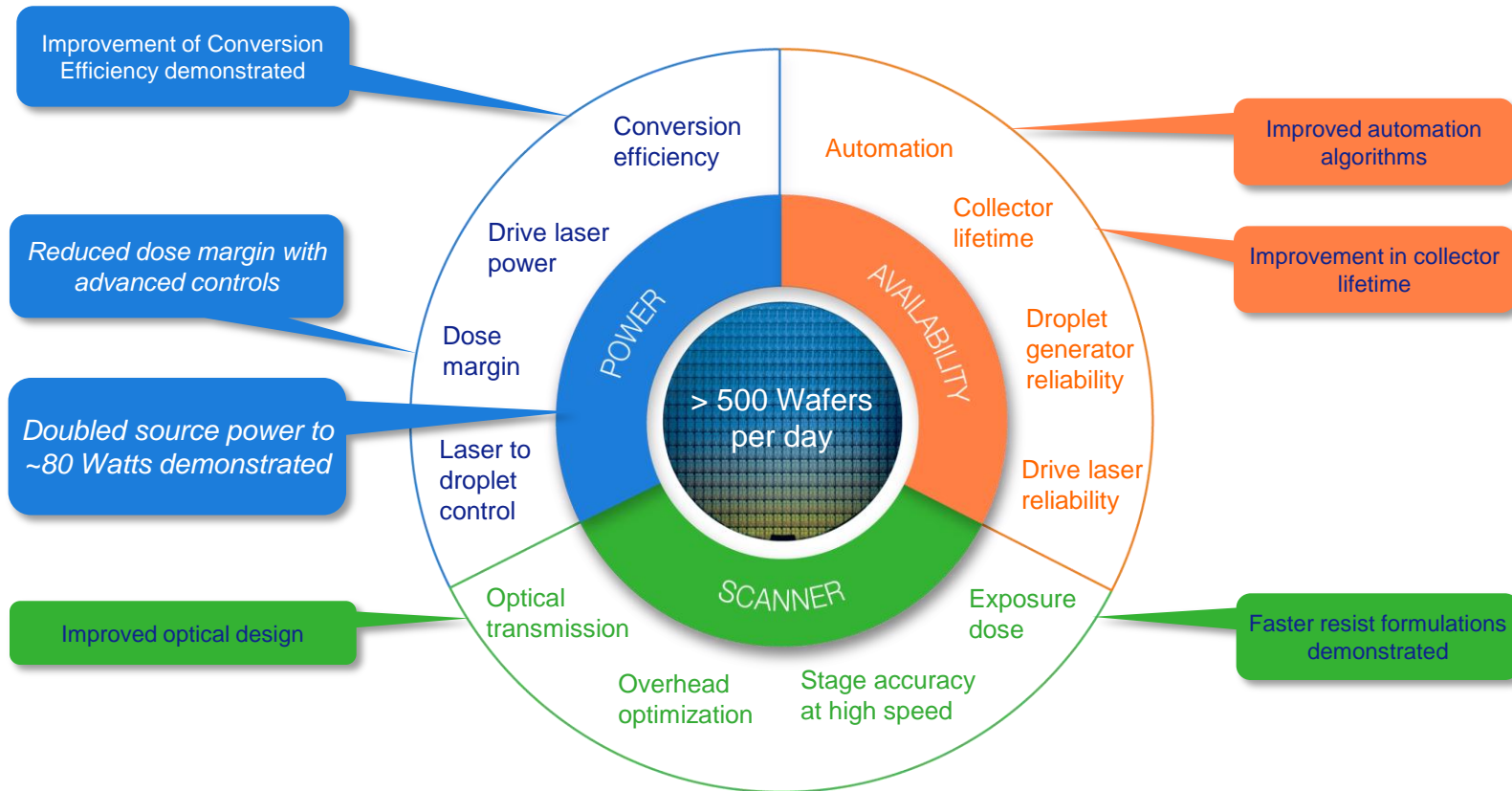
- More than 500 wafers exposed per day during endurance tests at 2 customer sites
- 7 NXE:3300B systems shipped to customers
- 4 more NXE:3300B systems being integrated
- 4th generation NXE system (NXE:3350B) integration ongoing
- EUV cleanroom extension is under construction

Agenda

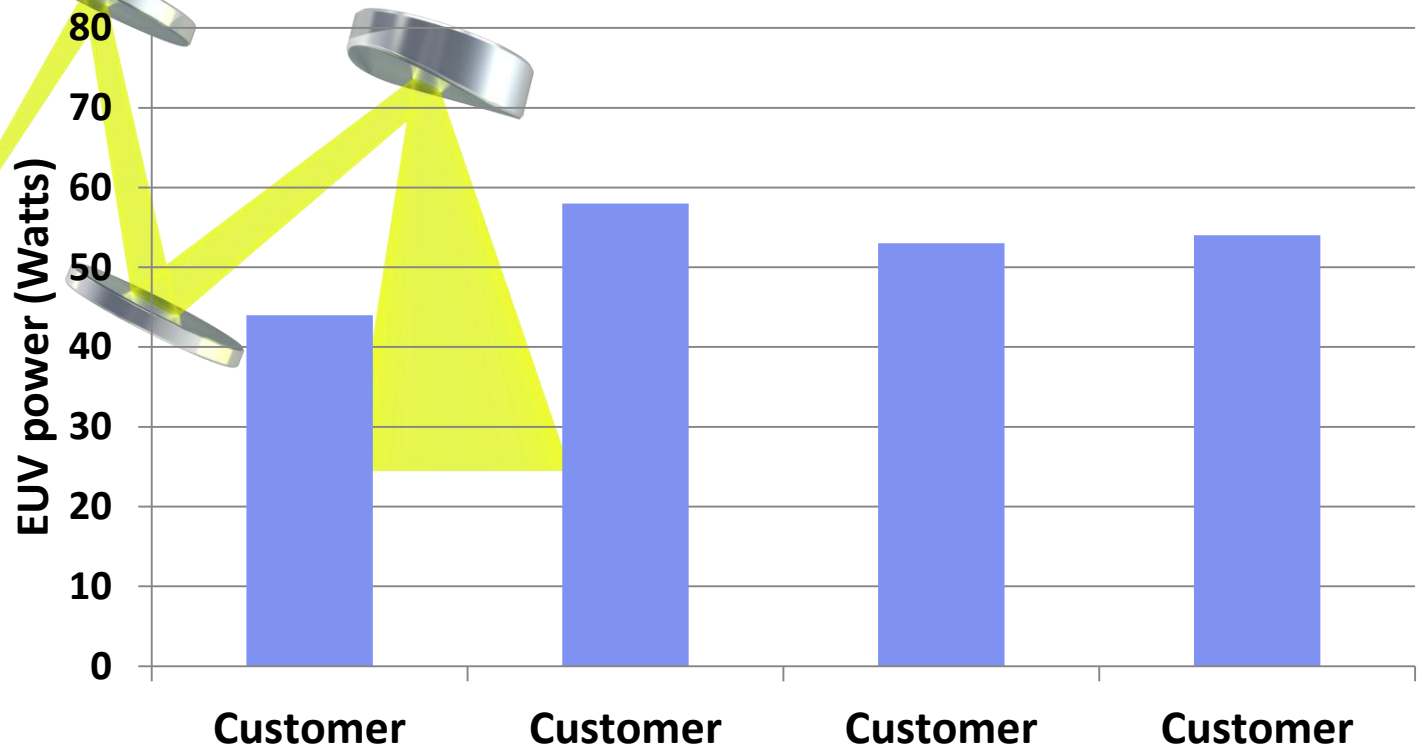
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Wafers per day program: Progress in major areas



>40W rolled-out on customer NXE:3300B systems

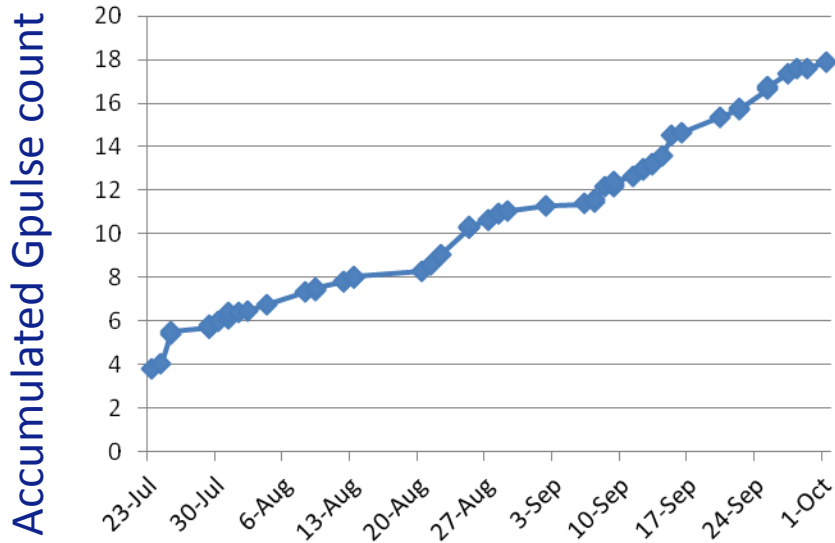


Under clean collector conditions

NXE:3300B customer systems

Customer system continuous use at power level of >40W

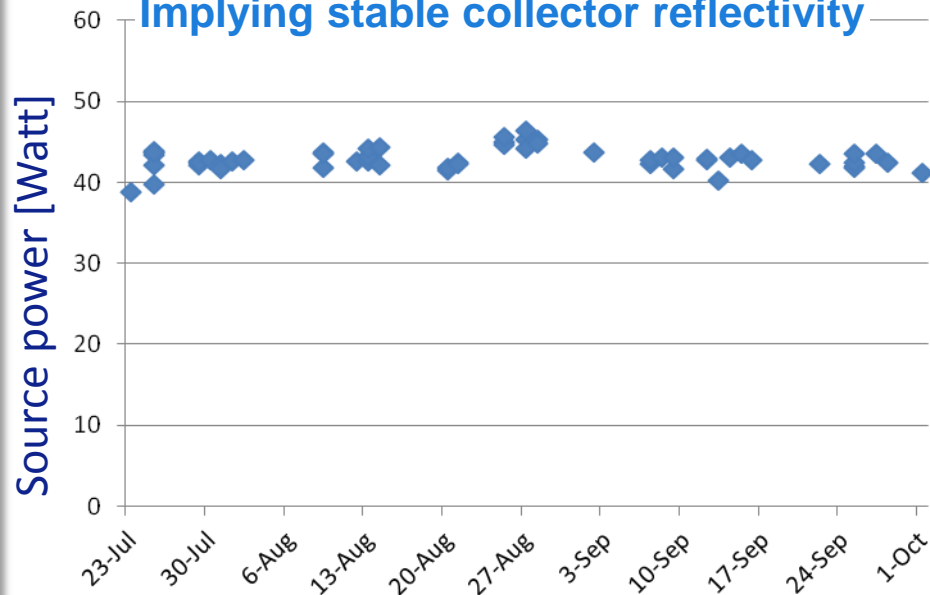
System pulse count



System continuously used

Power of >40W since start use system

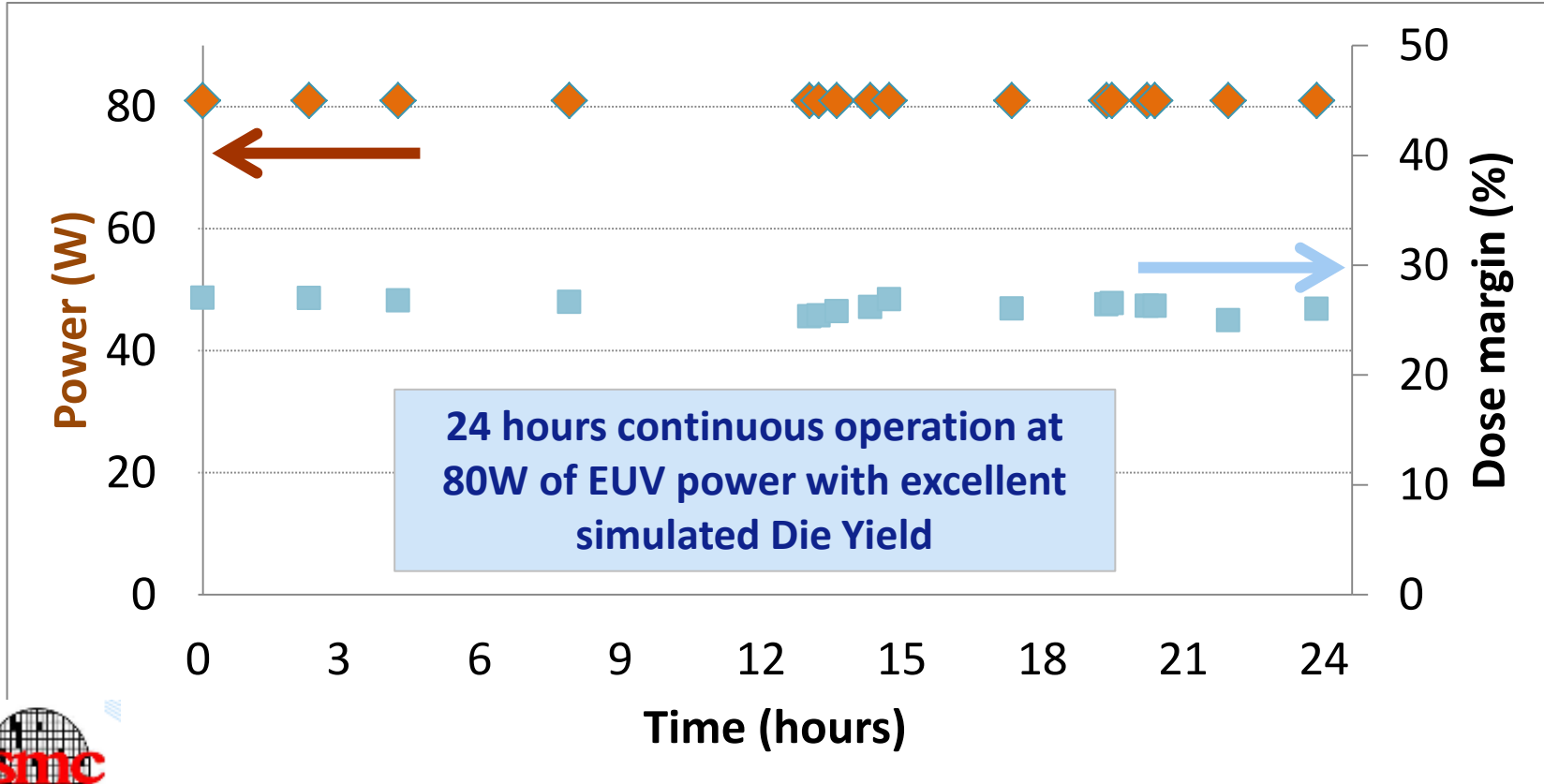
Implying stable collector reflectivity



Stable power over 2 months period of time

Continuous stable source operation at 80 W

excellent die yield, ~25% dose margin



Die Yield = Simulated % of dies that meet the 1% dose requirement

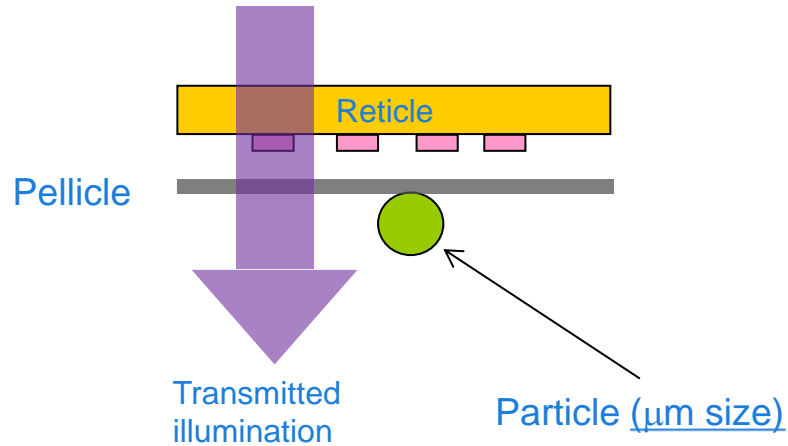
An Intermezzo

- Towards an pSi pellicle for EUV tools
- Source aspects

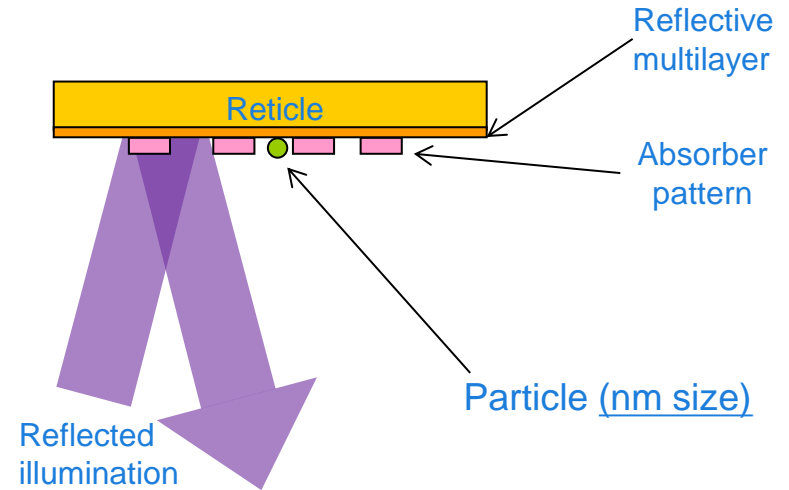
The mask defect challenge

Challenging defect requirements on reflective EUV mask without pellicle

DUV Reticles (193nm)



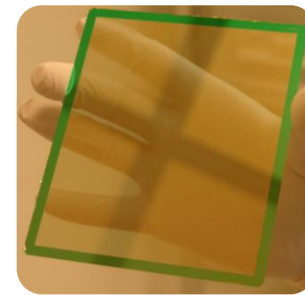
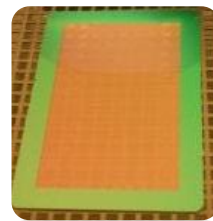
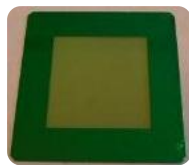
EUV Reticles (13.5nm)



Scalability of free-standing pSi films demonstrated and prototype pSi pellicles successfully tested in EUV tools

Full size prototype

Half size prototype

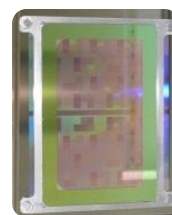
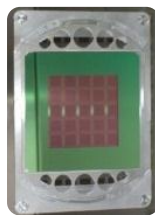
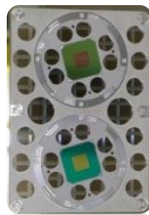


11mm x 11mm
(~80% EUV transmission)

50mm x 50mm
(~82% EUV transmission)

64mm x 106mm
~(86% EUV transmission)

103mm x 122mm
(~85% EUV transmission)

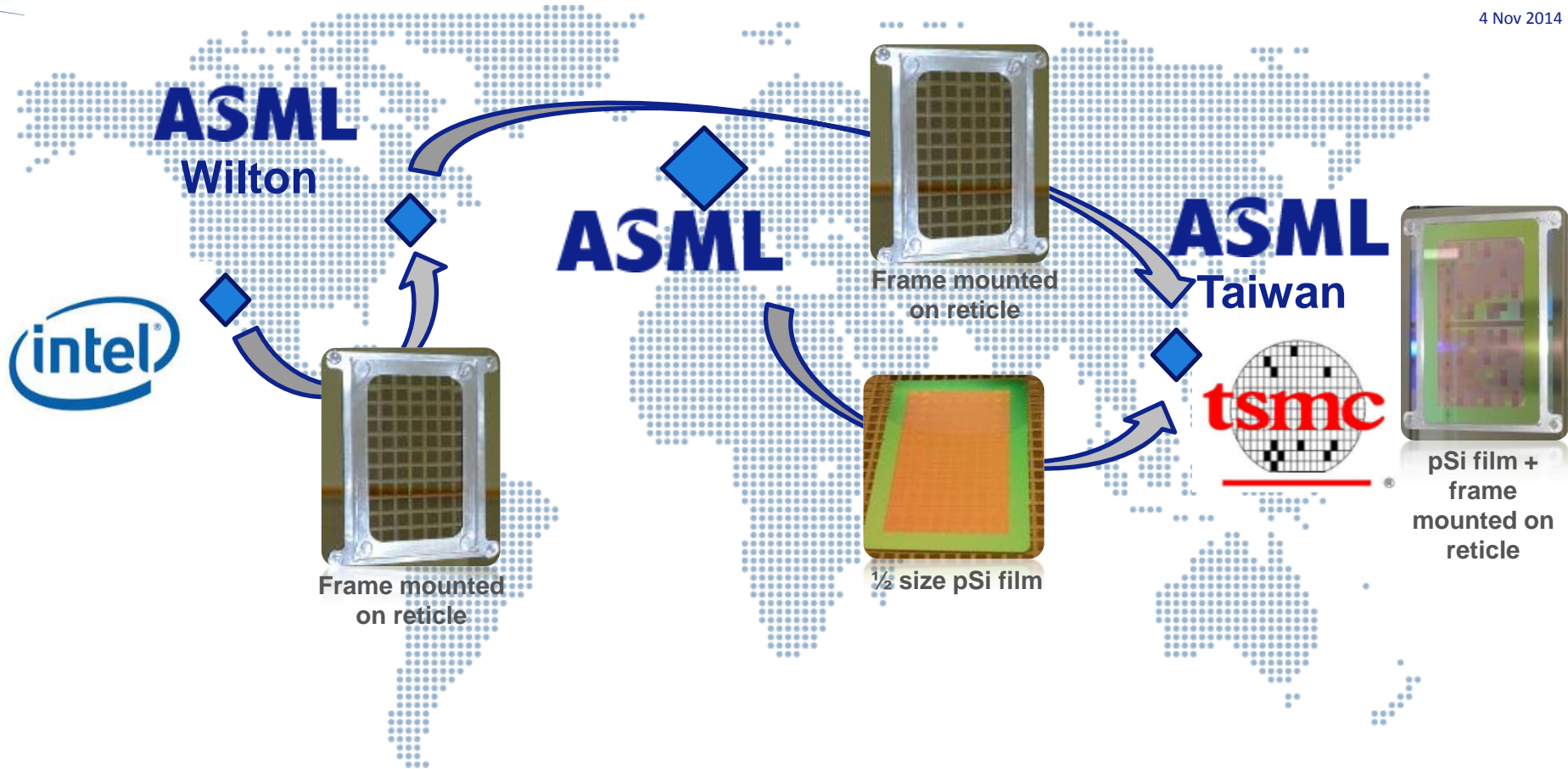


Open frames used for testing prototype pSi pellicles in EUV tools

All reticles and frames courtesy of Intel

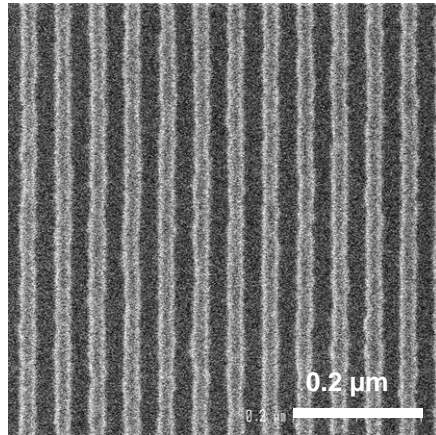


Imaging testing of 1/2 size pSi pellicle collaborative effort of ASML and customers



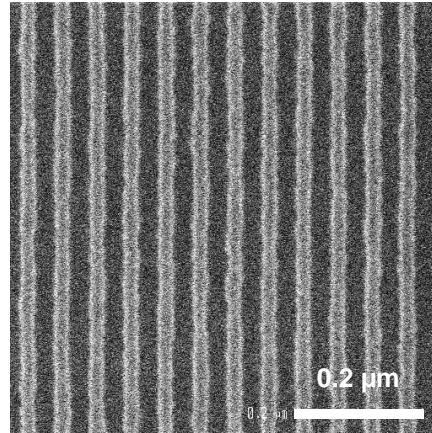
27 nm L/S features successfully exposed with half-size proto pellicle

SEM image at BE/BF
w/o pellicle



CD = 24.2 nm
LWR = 4.0 nm

SEM image at BE/BF
w/ pellicle



CD = 24.0 nm
LWR = 3.7 nm

- NXE:3100, NA=0.25, Conventional Illumination
- CDU difference of 0.18 nm
- Pellicle EUV transmission confirmed in imaging data: 85.5% (single pass)

Joint effort of NXE end users and ASML accomplished imaging results of half size pellicle

Source Aspects

LPP Source Architecture

- Key factors for high source power are:
 - High input CO₂ laser power
 - High conversion efficiency (CO₂ to EUV energy)
 - High collection efficiency (reflectivity and lifetime)
 - Advanced controls

Controllers for Dose and Prepulse

Fab Floor

Vessel
With Collector, Droplet
Generator and Metrology

Focusing
Optics

Beam Transport System

Prepulse
requires seed
laser trigger
control

Master Oscillator

Power Amplifier

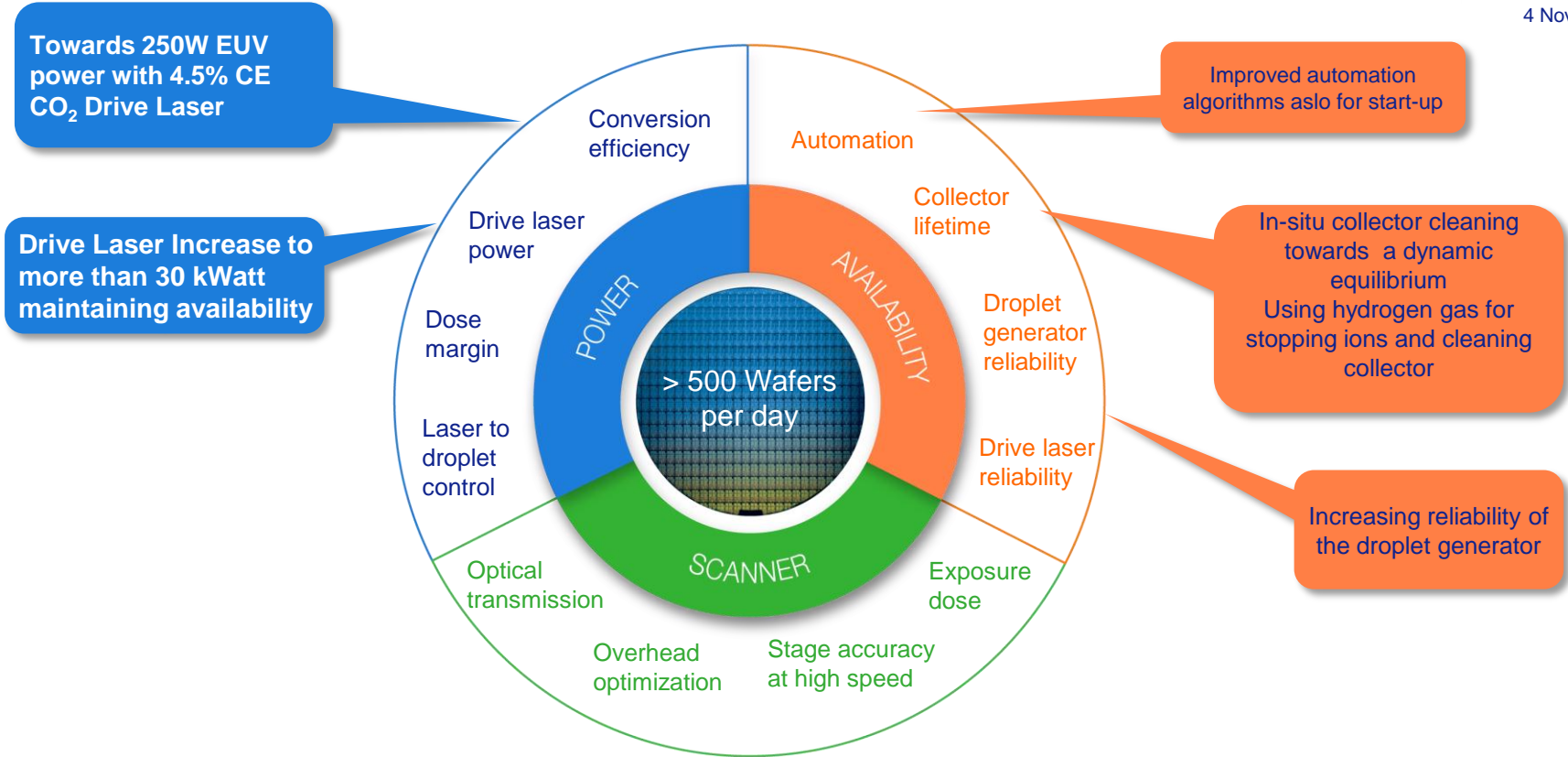
Sub-Fab Floor

MOPA - Master Oscillator Power Amplifier

ASML
EUVL
Symposium
Slide 20

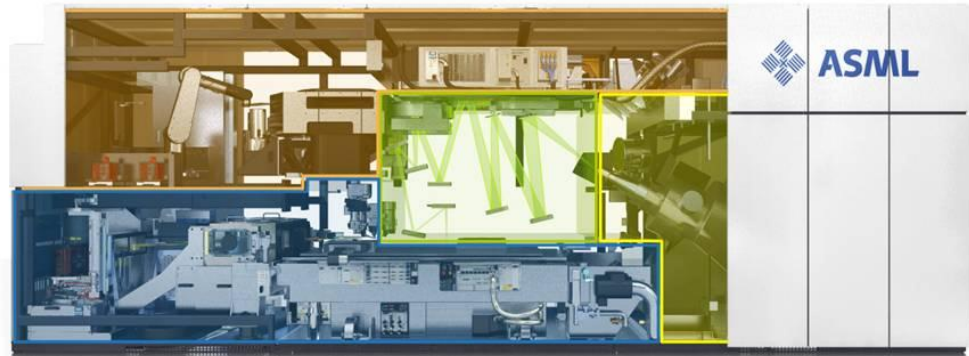
- Pre-pulse: Preparing Shape of Tin Target
- Main Pulse: Tin heating to proper state of matter (highly charged ions) and high temperature (200 kK) for continued EUV emission
- Pulse shaping in time and space for reduction of energy in particles and in ions and for increase of EUV radiation
- Protecting collector optics by hydrogen flow combining stopping and dynamic cleaning

250W / 125 wafers/hour LPP Power Scaling



Agenda

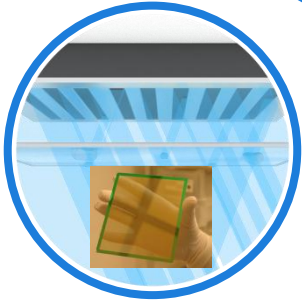
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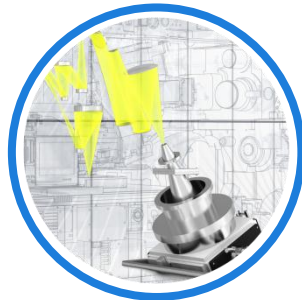
Summary: EUV towards production insertion



- Two customers demonstrated 500 wafer per day capability in endurance tests.
- System performance well within target at >40W source power



- Half-size EUV pellicle prototype has been tested successfully



- >40W stable performance at customers, 80W performance shown at ASML and being transferred to customers
- EUV source: Continuous Improvements on conversion efficiency, dose margin, automation, collector lifetime, driving power. Increasing reliability and availability

Acknowledgements

The work presented today, is the result of hard work and dedication of teams at ASML, Cymer, Zeiss, and many technology partners worldwide including our esteemed customers

Special thanks to our partners and customers for allowing us to use some of their data in this presentation

The image features the ASML logo in a bold, dark blue, sans-serif font on the left side. The background is a light blue gradient with several decorative elements: a large, semi-transparent, curved shape on the left; a series of thin, white, wavy lines that originate from the right side of the ASML text and extend across the bottom of the frame; and a solid light blue area at the top right.

ASML